

ABSTRACT OF THE DISCLOSURE

The processing with a low gate rate of destruction and high anisotropy is achieved in dry etching. Plasma is generated by ECR resonance of electromagnetic wave which arose by supplying Ultra High Frequency electric power in microstripline 4 arranged on the atmosphere side of a dielectric 2, which separates a vacuum inside and an outside and magnetic field. A conducting layer is etched by this plasma, which is stable and uniform plasma.